

IN THE SPECIFICATION

Please amend paragraph [0032] as follows:

Figs. 7 and 8 illustrate a vertical embodiment of the present invention. Like the device of Fig. 5, light is extracted from the device from the surface of contact layer 8. The resonant cavity is formed by DBR 4 and reflective metal layer 13. N-contact 10, which forms a ring around contact layer 8, electrically contacts the n-side of the device. A portion of reflective metal layer 13 electrically contacts the p-side of the device. The host substrate bonded to contact layer 3 includes conductive regions 16 and 17 and insulating layer 12, which electrically connect to n-contact 10 and reflective p-contact 13. Host substrate 12 may be, for example, a silicon substrate, and conductive regions 16 and 17 may be metals or heavily doped semiconductor regions. Contact 10 connects to conductive region 16 by a layer of contact material extending down one or more sides of epitaxial layers 14. Layers 14 are electrically isolated from the contact material by an insulating layer 15. The portions of reflective metal layer 13 electrically connected to p-contact conductive region 17 and n-contact conductive region 16 are also isolated by an insulating layer 15. The device illustrated in Figs. 7 and 8 may be surface mounted on another device by, for example, solder joints electrically and physically connected to the back side of conductive regions 16 and 17. Examples of host substrates surface mountable in this manner are described in more detail in ~~Application Serial No. [Attorney Docket Number LUM-M-12418-US]~~, filed July 31, 2003, U.S. Patent No. 6,876,008, granted April 5, 2005, titled "Mount for Semiconductor Light Emitting Device," and incorporated herein by this reference.

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